

ON Semiconductor®

FDC6331L

Integrated Load Switch

General Description

This device is particularly suited for compact power management in portable electronic equipment where 2.5V to 8V input and 2.8A output current capability are needed. This load switch integrates a small N-Channel power MOSFET (Q1) that drives a large PChannel power MOSFET (Q2) in one tiny SuperSOTTM-6 package.

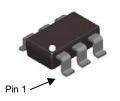
Applications

- · Load switch
- Power management

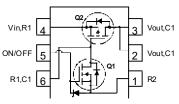


Features

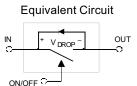
- -2.8 A, -8 V. $R_{DS(ON)}$ = 55 m Ω @ V_{GS} = -4.5 V $R_{DS(ON)}$ = 70 m Ω @ V_{GS} = -2.5 V $R_{DS(ON)}$ = 100 m Ω @ V_{GS} = -1.8 V
- Control MOSFET (Q1) includes Zener protection for ESD ruggedness (>6KV Human body model)
- \bullet High performance trench technology for extremely low $R_{\text{DS}(\text{ON})}$







See Application Circuit



Absolute Maximum Ratings T_A=25°C unless otherwise noted

Symbol	Parameter	Ratings	Units
V _{IN}	Maximum Input Voltage	± 8	V
V _{ON/OFF}	High level ON/OFF voltage range	-0.5 to 8	V
Load	Load Current - Continuous (Note 1)	2.8	Α
	– Pulsed	9	
P _D	Maximum Power Dissipation (Note 1)	0.7	W
TJ, TSTG	Operating and Storage Junction Temperature Range	-55 to +150	°C

Thermal Characteristics

$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	(Note 1)	180	°C/W
R _{⊕JC}	Thermal Resistance, Junction-to-Case	(Note 1)	60	°C/W

Package Marking and Ordering Information

Device Marking	Device	Reel Size	Tape width	Quantity
.331	FDC6331L	7"	8mm	3000 units

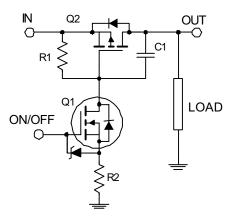
Electrical Characteristics T _A = 25°C unless otherwise noted							
Symbol	Parameter	Test Conditions	Min	Тур	Max	Units	
Off Char	acteristics				•	•	
BV _{IN}	Vin Breakdown Voltage	$V_{ON/OFF} = 0 \text{ V}, I_D = -250 \mu\text{A}$	8			V	
Load	Zero Gate Voltage Drain Current	V _{IN} = 6.4 V, V _{ON/OFF} = 0 V			-1	μΑ	
I _{FL}	Leakage Current, Forward	V _{ON/OFF} = 0 V, V _{IN} = 8 V			-100	nA	
I _{RL}	Leakage Current, Reverse	V _{ON/OFF} = 0 V, V _{IN} = -8 V			100	nA	
On Char	acteristics (Note 2)						
V _{ON/OFF (th)}	Gate Threshold Voltage	$V_{IN} = V_{ON/OFF}, I_D = -250 \mu A$	0.4	0.9	1.5	V	
R _{DS(on)}	Static Drain–Source On–Resistance (Q2)	$V_{GS} = -4.5 \text{ V},$ $I_D = -2.8 \text{A}$ $V_{GS} = -2.5 \text{ V},$ $I_D = -2.5 \text{ A}$ $V_{GS} = -1.8 \text{ V},$ $I_D = -2.0 \text{ A}$		34 45 64	55 70 100	mΩ	
$R_{DS(on)}$	Static Drain–Source On–Resistance (Q1)	$V_{GS} = 4.5 \text{ V}, \qquad I_D = 0.4 \text{A} $ $V_{GS} = 2.7 \text{ V}, \qquad I_D = 0.2 \text{ A}$		3.1 3.8	4 5	Ω	

Drain-Source Diode Characteristics and Maximum Ratings

ls	Maximum Continuous Drain-Source Diode Forward Current			-0.6	Α
V_{SD}	Drain–Source Diode Forward Voltage	$V_{ON/OFF} = 0 \text{ V}, I_S = -0.6 \text{ A} \text{ (Note 2)}$		-1.2	V

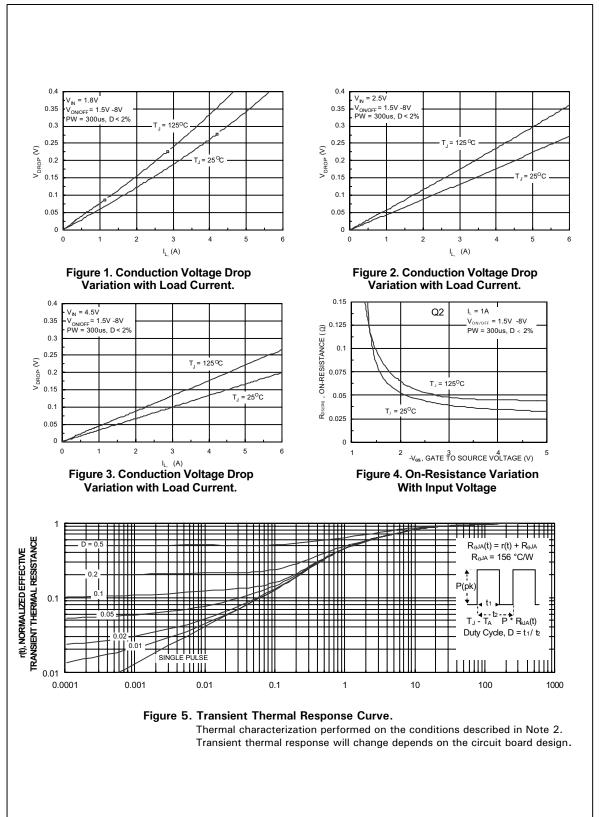
- Notes:
 1. R _{8JA} is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. R $_{\theta JC}$ is guaranteed by design while R $_{\theta JA}$ is determined by the user's board design.
- 2. Pulse Test: Pulse Width < 300 μ s, Duty Cycle < 2.0%.

FDC6331L Load Switch Application Circuit



External Component Recommendation:

For additional in-rush current control, R2 and C1 can be added. For more information, see application note AN1030.



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